

OfficialAMENDMENT TO THE SPECIFICATION:421-03
3/21/03

After forming the gate and the electrode located at the same layer, a gate insulating film 7 and a semiconductor film forming active layers of the TFTs 1 and 4 are successively formed in this order through plasma CVD over the entire substrate. As the gate insulating film 7, a Si nitride film of about 500 Å and a Si oxide film of about 1300 Å are successively formed in this order from the bottom, and then an a-Si film of about 500 Å is formed. The semiconductor film first formed as described above an a-Si film is then turned into a p-Si film through an annealing process as described hereinafter, and used for the active layers 12 and 16 and a second capacitor electrode 3 which is an upper electrode of the storage capacitor 8. It is also noted that active layer 12 includes a first conductive region and a second conductive region and that active layer 16 includes a third conductive region IR2 and a fourth conductive region IR1.

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